

# MOSFET - Power, Single N-Channel, STD Gate, DUAL COOL<sup>®</sup> DFN8 5x6 60 V, 1.5 mΩ, 238 A

## Product Preview NTMFSC1D6N06C

### Features

- Advanced Dual-sided Cooled Packaging
- Low  $R_{DS(on)}$  to Minimize Conduction Losses
- Low  $Q_G$  and Capacitance to Minimize Driver Losses
- These Devices are Pb-Free and are RoHS Compliant

### Typical Applications

- Synchronous Rectifier
- DC-DC Conversion
- Oring FET and Load Switching

### MAXIMUM RATINGS ( $T_J = 25^\circ\text{C}$ unless otherwise noted)

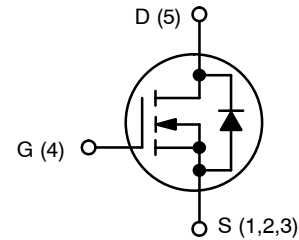
Parameter			Symbol	Value	Unit
Drain-to-Source Voltage			V <sub>DSS</sub>	60	V
Gate-to-Source Voltage			V <sub>GS</sub>	±20	V
Continuous Drain Current R <sub>θJC</sub> (Notes 1, 3)	Steady State	T <sub>C</sub> = 25°C	I <sub>D</sub>	238	A
		T <sub>C</sub> = 100°C		168	
Power Dissipation R <sub>θJC</sub> (Note 1)	Steady State	T <sub>C</sub> = 25°C	P <sub>D</sub>	170	W
		T <sub>C</sub> = 100°C		84	
Continuous Drain Current R <sub>θJA</sub> (Notes 1, 2, 3)	Steady State	T <sub>A</sub> = 25°C	I <sub>D</sub>	35	A
		T <sub>A</sub> = 100°C		25	
Power Dissipation R <sub>θJA</sub> (Notes 1, 2)	Steady State	T <sub>A</sub> = 25°C	P <sub>D</sub>	3.8	W
		T <sub>A</sub> = 100°C		1.9	
Pulsed Drain Current	T <sub>A</sub> = 25°C, t <sub>p</sub> = 10 μs		I <sub>DM</sub>	900	A
Operating Junction and Storage Temperature Range			T <sub>J</sub> , T <sub>stg</sub>	-55 to +175	°C
Source Current (Body Diode)			I <sub>S</sub>	190	A
Single Pulse Drain-to-Source Avalanche Energy (I <sub>L(pk)</sub> = 17 A)			E <sub>AS</sub>	451	mJ
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)			T <sub>L</sub>	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

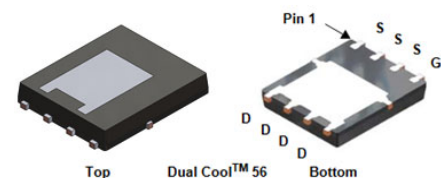
1. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
2. Surface-mounted on FR4 board using a 650 mm<sup>2</sup>, 2 oz. Cu pad.
3. Maximum current for pulses as long as 1 second is higher but is dependent on pulse duration and duty cycle.

This document contains information on a product under development. onsemi reserves the right to change or discontinue this product without notice.

$V_{(BR)DSS}$	$R_{DS(ON)} \text{ MAX}$	$I_D \text{ MAX}$
60 V	1.5 mΩ @ 10 V	238 A

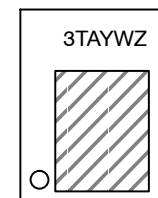


N-CHANNEL MOSFET



DFN8 5x6  
CASE 506EG

### MARKING DIAGRAM



- 3T = Specific Device Code  
A = Assembly Location  
Y = Year  
W = Work Week  
Z = Assembly Lot Code

### ORDERING INFORMATION

See detailed ordering and shipping information on page 6 of this data sheet.

# NTMFSC1D6N06C

## THERMAL RESISTANCE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case (Bottom)	$R_{\theta JC}$	0.9	°C/W
Thermal Resistance, Junction-to-Case (Top)	$R_{\theta JC}$	1.4	
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	39	

## ELECTRICAL CHARACTERISTICS ( $T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
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### OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	60			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$\Delta V_{(BR)DSS} / \Delta T_J$	$I_D = 250\text{ }\mu\text{A}$ , Referenced to $25^\circ\text{C}$		12.8		mV/°C
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 60\text{ V}, T_J = 25^\circ\text{C}$			10	$\mu\text{A}$
		$V_{DS} = 60\text{ V}, T_J = 125^\circ\text{C}$			250	
Gate-to-Source Leakage Current	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = 20\text{ V}$			100	nA

### ON CHARACTERISTICS (Note 4)

Drain-to-Source On Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 50\text{ A}$		1.27	1.5	m $\Omega$
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 250\text{ }\mu\text{A}$	2.0		4.0	V
Gate Threshold Voltage Temperature Coefficient	$\Delta V_{GS(TH)} / \Delta T_J$	$V_{GS} = V_{DS}, I_D = 250\text{ }\mu\text{A}$		-9.4		mV/°C
Forward Transconductance	$g_{FS}$	$V_{DS} = 5\text{ V}, I_D = 50\text{ A}$		157		S

### CHARGES, CAPACITANCES & GATE RESISTANCE

Input Capacitance	$C_{ISS}$	$V_{GS} = 0\text{ V}, V_{DS} = 30\text{ V}, f = 1\text{ MHz}$		4860		pF
Output Capacitance	$C_{OSS}$			2800		
Reverse Transfer Capacitance	$C_{RSS}$			40		
Output Charge	$Q_{OSS}$	$V_{GS} = 10\text{ V}, V_{DD} = 30\text{ V}, I_D = 50\text{ A}$		128		nC
Total Gate Charge	$Q_{G(TOT)}$			65		
Threshold Gate Charge	$Q_{G(TH)}$			13		
Gate-to-Source Charge	$Q_{GS}$			22		
Gate-to-Drain Charge	$Q_{GD}$			11		
Gate Resistance	$R_G$	$f = 1\text{ MHz}$		2		$\Omega$
Gate Voltage Plateau	$V_{GP}$			4.6		V

### SWITCHING CHARACTERISTICS (Note 5)

Turn-On Delay Time	$t_{d(ON)}$	Resistive Load, $V_{GS} = 0/10\text{ V}$ , $V_{DD} = 30\text{ V}, I_D = 50\text{ A}, R_G = 2.5\text{ }\Omega$		26		ns
Rise Time	$t_r$			8		
Turn-Off Delay Time	$t_{d(OFF)}$			50		
Fall Time	$t_f$			9		

# NTMFSC1D6N06C

## ELECTRICAL CHARACTERISTICS ( $T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
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### SOURCE-TO-DRAIN DIODE CHARACTERISTICS

Forward Diode Voltage	$V_{SD}$	$V_{GS} = 0\text{ V}, I_S = 50\text{ A}, T_J = 25^\circ\text{C}$		0.81	1.2	V
		$V_{GS} = 0\text{ V}, I_S = 50\text{ A}, T_J = 125^\circ\text{C}$		0.67		
Reverse Recovery Time	$t_{RR}$	$V_{GS} = 0\text{ V}, I_S = 50\text{ A}$ $di/dt = 100\text{ A}/\mu\text{s}$		82		ns
Charge Time	$t_a$			41		
Discharge Time	$t_b$			41		
Reverse Recovery Charge	$Q_{RR}$			139		nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Pulse Test: pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .

5. Switching characteristics are independent of operating junction temperatures.

TYPICAL CHARACTERISTICS

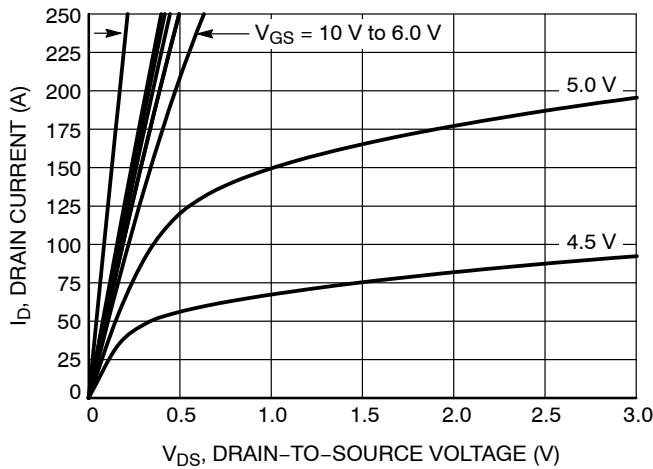


Figure 1. On-Region Characteristics

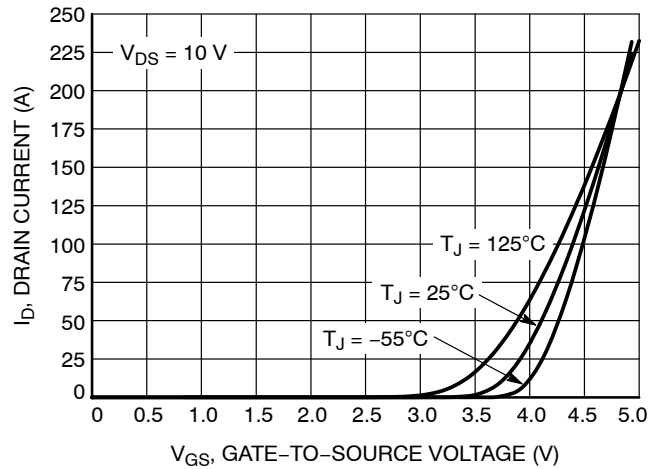


Figure 2. Transfer Characteristics

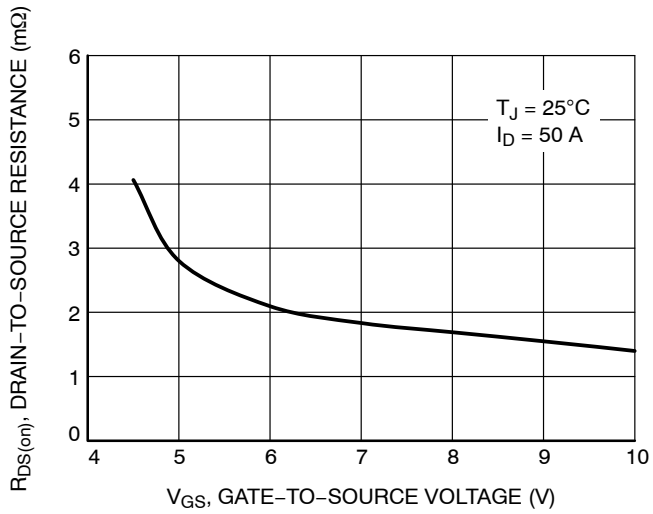


Figure 3. On-Resistance vs. Gate-to-Source Voltage

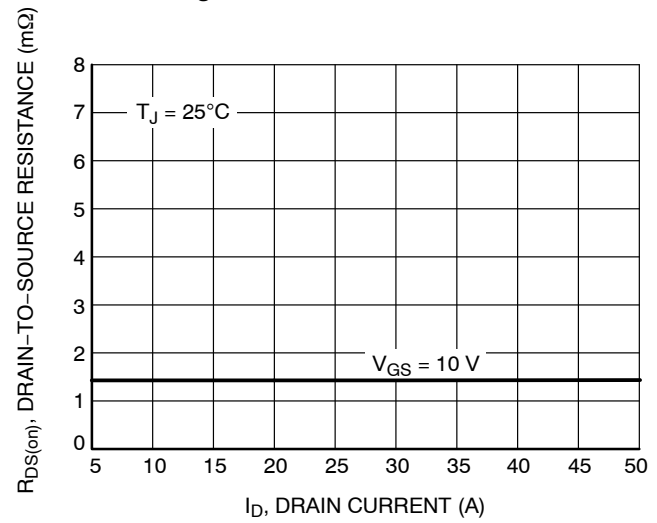


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

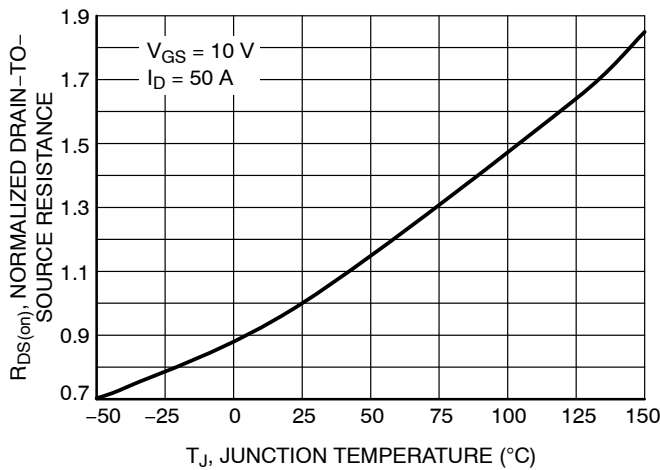


Figure 5. On-Resistance Variation with Temperature

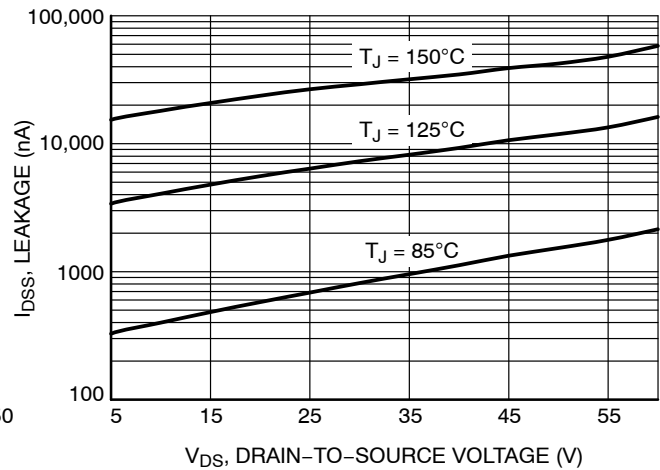


Figure 6. Drain-to-Source Leakage Current vs. Voltage

# NTMFSC1D6N06C

## TYPICAL CHARACTERISTICS

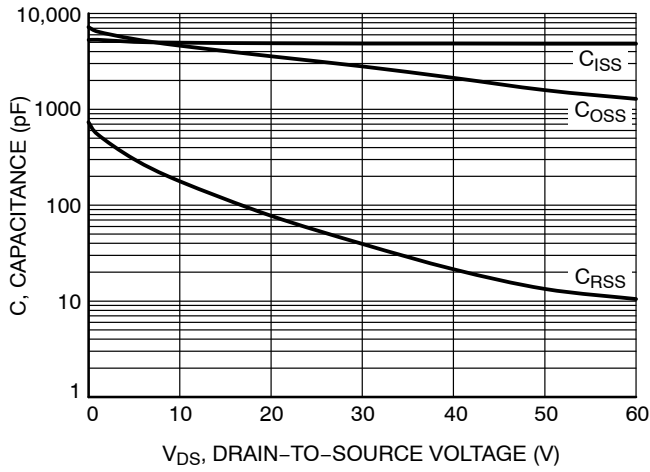


Figure 7. Capacitance Variation

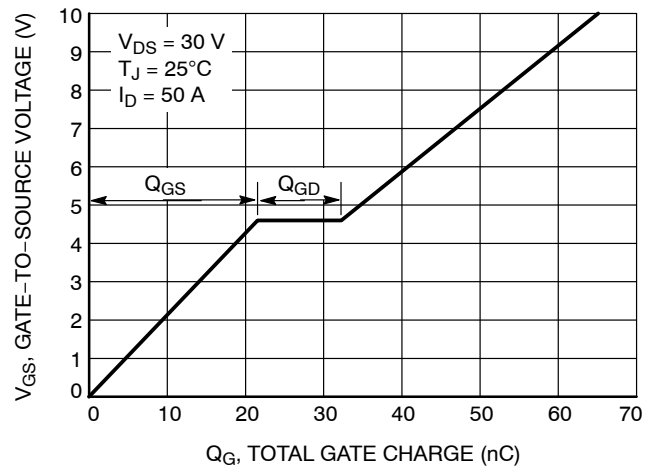


Figure 8. Gate Charge Characteristics

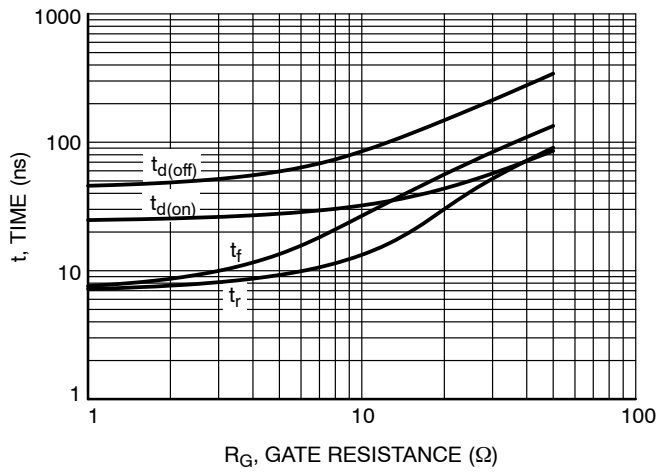


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

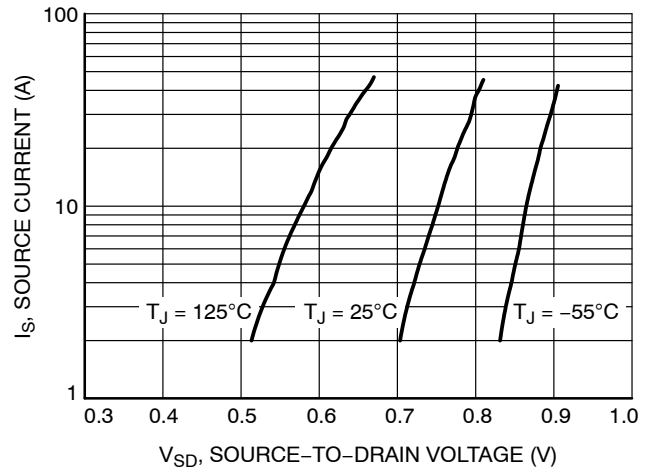


Figure 10. Diode Forward Voltage vs. Current

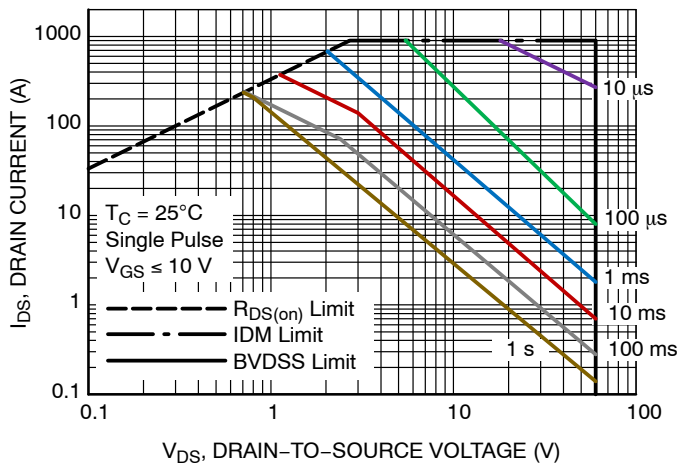


Figure 11. Safe Operating Area

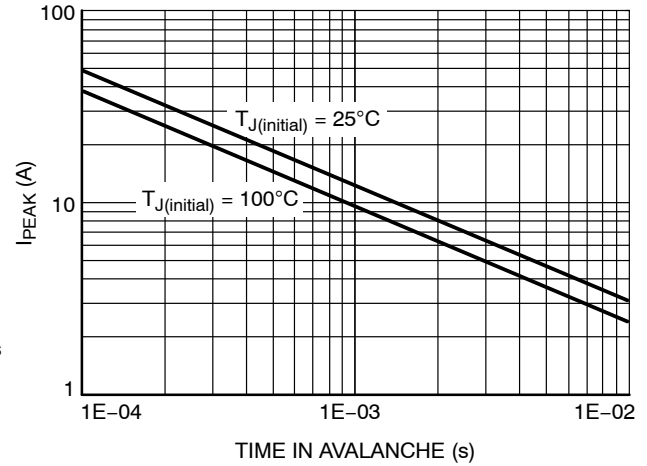


Figure 12.  $I_{PEAK}$  vs. Time in Avalanche

# NTMFSC1D6N06C

## TYPICAL CHARACTERISTICS

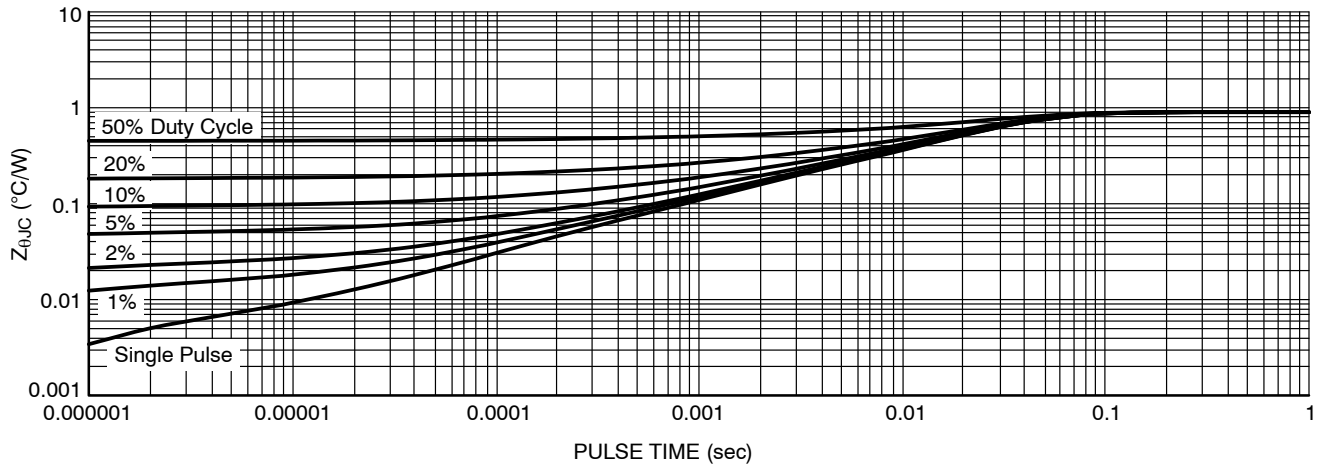


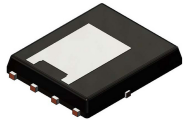
Figure 13. Thermal Characteristics

## ORDERING INFORMATION

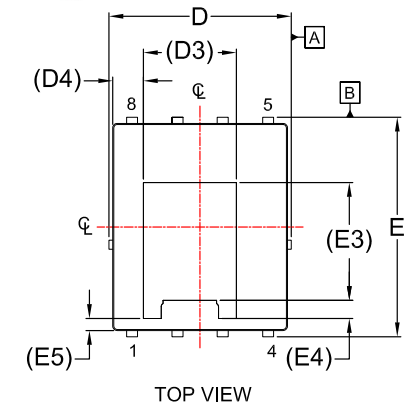
Device	Device Marking	Package	Shipping <sup>†</sup>
NTMFSC1D6N06CTWG	3T	DFN8 5x6 (Pb-Free/Halogen Free)	3000 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

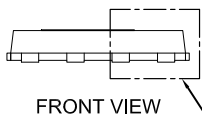
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**CASE 506EG**  
**ISSUE D**

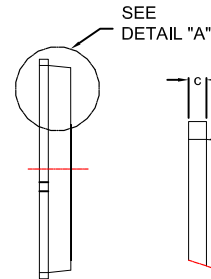
DATE 25 AUG 2020



TOP VIEW



FRONT VIEW

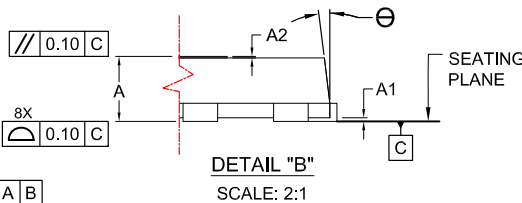
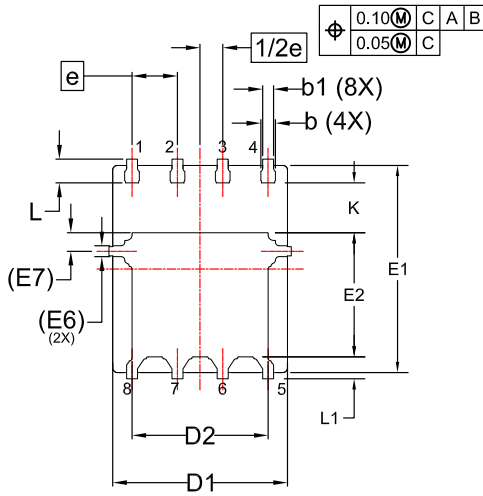


SIDE VIEW

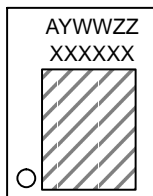
DETAIL "A"  
SCALE: 2:1

## NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
2. CONTROLLING DIMENSION: MILLIMETERS
3. COPLANARITY APPLIES TO THE EXPOSED PADS AS WELL AS THE TERMINALS.
4. DIMENSIONS D1 AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.
5. SEATING PLANE IS DEFINED BY THE TERMINALS. "A1" IS DEFINED AS THE DISTANCE FROM THE SEATING PLANE TO THE LOWEST POINT ON THE PACKAGE BODY.


DETAIL "B"  
SCALE: 2:1


BOTTOM VIEW

**GENERIC MARKING DIAGRAM\***


XXXX = Specific Device Code  
A = Assembly Location  
Y = Year  
WW = Work Week  
ZZ = Assembly Lot Code

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.85	0.90	0.95
A1	-	-	0.05
A2	-	-	0.05
b	0.31	0.41	0.51
b1	0.21	0.31	0.41
c	0.20	0.25	0.30
D	4.90	5.00	5.10
D1	4.80	4.90	5.00
D2	3.67	3.82	3.97
D3	2.60 REF		
D4	0.86 REF		
E	6.05	6.15	6.25
E1	5.70	5.80	5.90
E2	3.38	3.48	3.58
E3	3.30 REF		
E4	0.50 REF		
E5	0.34 REF		
E6	0.30 REF		
E7	0.52 REF		
e	1.27 BSC		
1/2e	0.635 BSC		
K	1.30	1.40	1.50
L	0.56	0.66	0.76
L1	0.52	0.62	0.72
Θ	0°	---	12°

LAND PATTERN RECOMMENDATION  
\*FOR ADDITIONAL INFORMATION ON OUR PB-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

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<b>DESCRIPTION:</b>	<b>DFN8 5x6.15, 1.27P, DUAL COOL</b>	<b>PAGE 1 OF 1</b>

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